

Forward Tracker Disks for the DBD

IX Jornadas Futuros Aceleradores
IFIC, Valencia



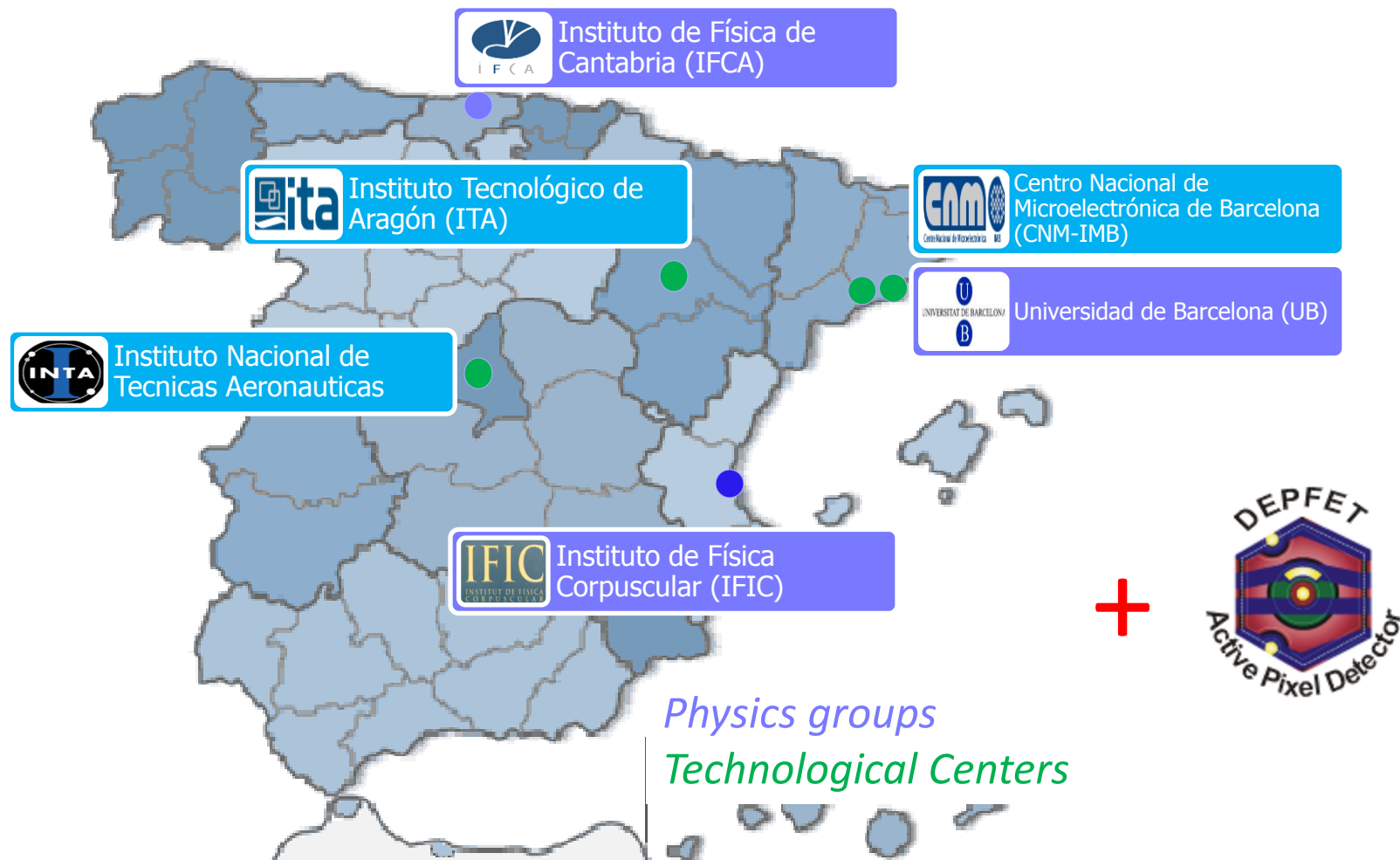
I. Vila

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Thanks to F. Arteché (ITA), A. Dieguez (UB), M. Frovel (INTA), D. Moya (IFCA) & M. Vos (IFIC) for their supporting material

FTD community at a Glance

Part of Spanish Network on Future accelerators



Outline

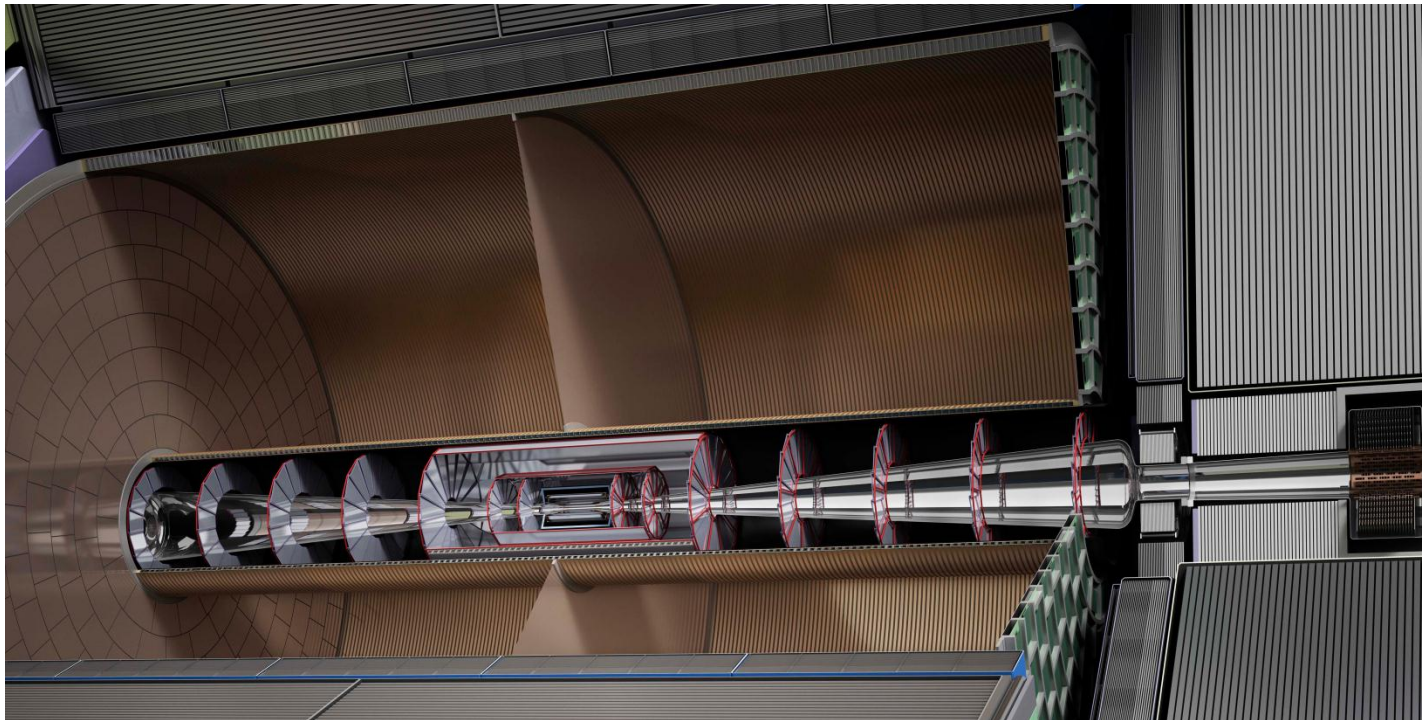


- FTD baseline design (DBD implementation) :
 - _ Pixelated disks: DEPFET & CPS
 - _ Strip Petal design: sensors and hybrids.
 - _ Mechanics, integration & services
 - _ Front-end electronics.
 - _ Power distribution & EMC.
 - _ Alignment and monitoring.
- Beyond the baseline design (R&D activities).
 - _ 2D strips sensors, miniaturized position sensors and low noise powering.

Introduction: baseline design

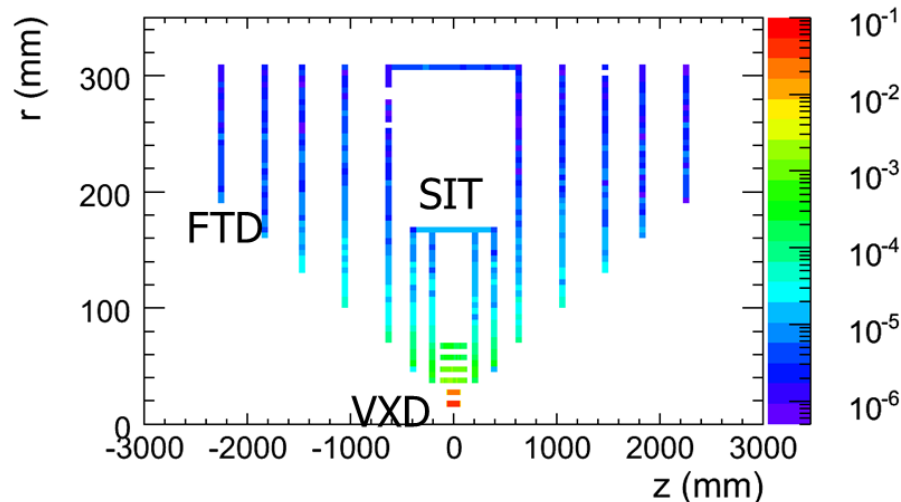


- Seven layers (disk) covering the forward and backward region between the TPC and the beam pipe.
- Inner two disks (inside thermal enclosure ?) pixelated single layer of silicon sensors and five outer disks equipped with a double layer of strip-based silicon sensors.



Layout optimization: why pixels ?

Pair background



Hit density
($\text{\#}/\text{mm}^2/\text{BX}$)

detector	min	typical	max
VXD 1		4×10^{-2}	
VXD 6		3×10^{-4}	
FTD1	$< 10^{-5}$	1×10^{-4}	2×10^{-3}
FTD7	5×10^{-6}	7×10^{-6}	9×10^{-6}
SIT 1		3×10^{-5}	
SIT 2		3×10^{-6}	

GEANT4 simulation of GUINEA-PIG events by Toni Harlin
(thanks also to A. Vogel and Katarzyna Wichman)

Hit density = number of GEANT4 energy deposits per unit area per ILC bunch crossing
Does not take into account the number of channels fired by a single hit

pixel:

Typical area sensitive elements

$$25 \times 25 \text{ mm}^2 = 6.25 \times 10^{-4} \text{ mm}^2$$

time resolution:

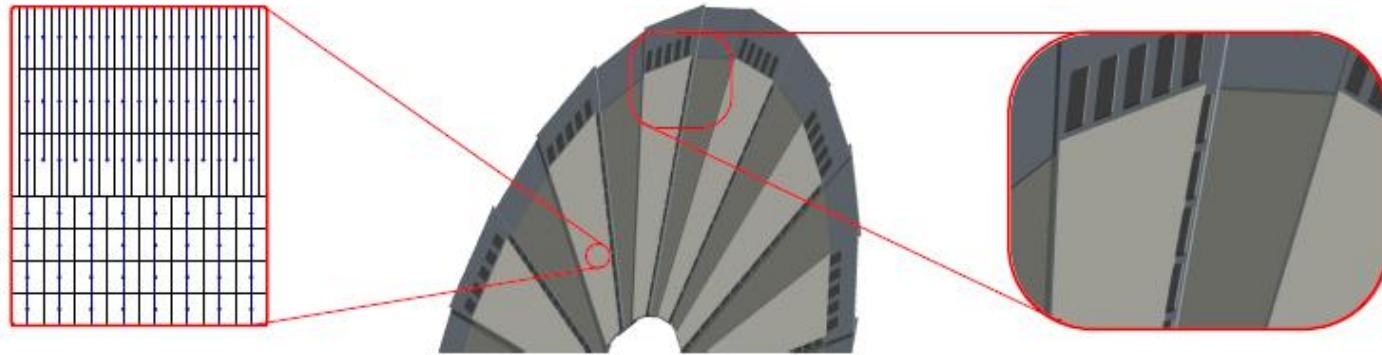
100 BX

strips:

$$50 \text{ mm} \times 10 \text{ cm} = 0.5 \text{ mm}^2$$

1 BX

Pixelated disks: DEPFET implementation



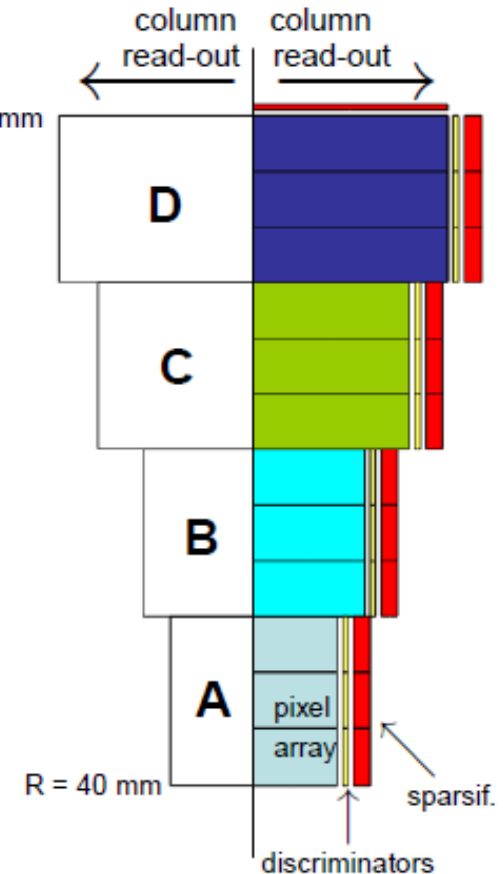
- Adaptation of the barrel ladder concept.
- To cope with the strongly increasing background levels towards the smallest R values. Radially three pixel dimensions are used:
 - 25 μm in the innermost region; 50 μm for $6\text{ cm} < R < 8\text{ cm}$; 100 μm for $R > 8\text{ cm}$.
- Rphi resolution from 3-5 μm depending of the radius

Pixelated disks: CMOS Implementation



- 16 petals made of 4 sensors ($50\ \mu\text{m}$ thin) on station front & back ($\Delta\phi = \pi/8\ \text{rad}$)
 \Rightarrow 4 impact positions per track traversing end-cap ($\sim 0.5\ \% X_0/\text{station}$)
- Sensors' sensitive area: from 30×28 to $30 \times 64\ \text{mm}^2$
- Each sensor combines 2 sub-arrays read out on opposite sides
- Each sub-array composed of 1152 columns of 480 pixels
- Column // read-out via pairs of rows (200 ns/pair) $\Rightarrow t_{r.o.} \sim 50\ \mu\text{s}$
- Binary charge encoding and integrated data sparsification
- Instantaneous power: $2.4\ \text{W}/\text{chip} \Rightarrow \lesssim 10\ \text{W}/\text{petal}$
 $\Rightarrow P_{inst. endcap} \sim 600\ \text{W} \Rightarrow \overline{P}_{endcap} \sim O(10)\ \text{W} \Rightarrow$ air cooling OK

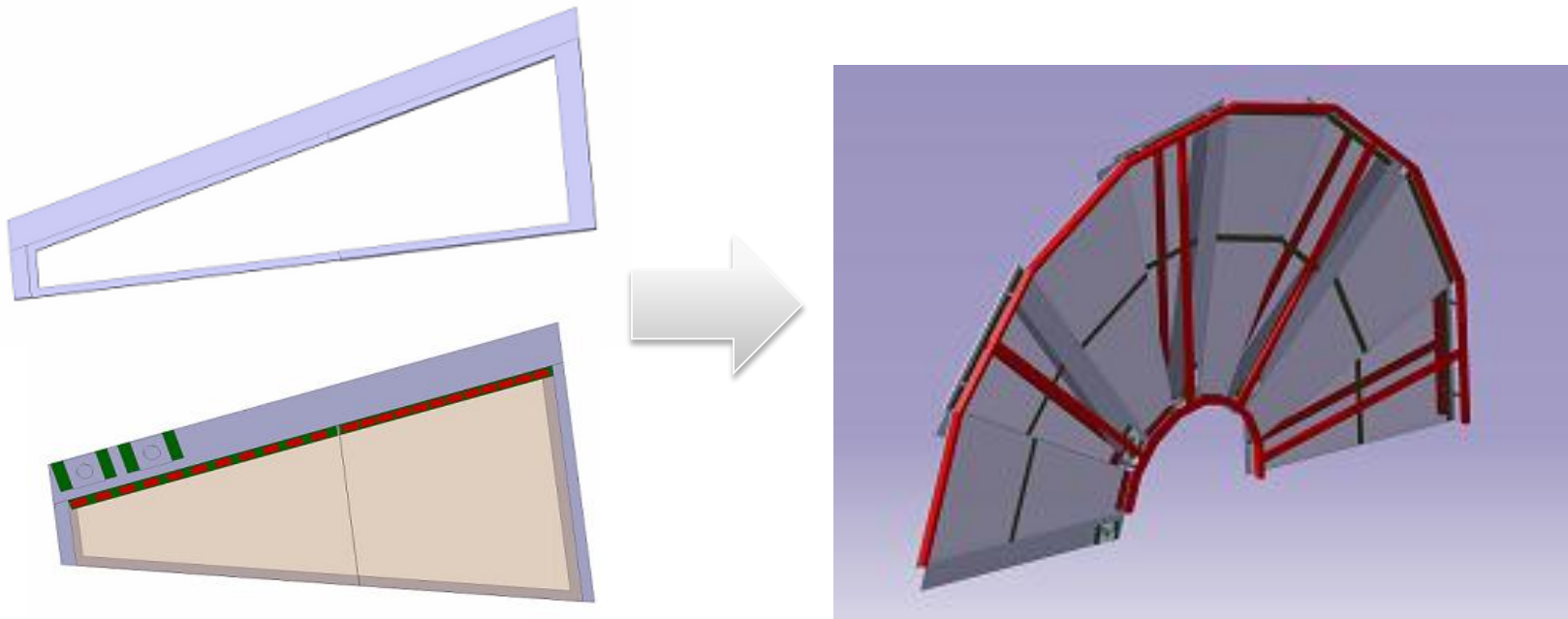
Sensor	R_{min} - R_{max}	column length	pixel dimensions	spatial resolution
A	40-70 mm	14 mm	$26 \times 29\ \mu\text{m}^2$	$\lesssim 6\ \mu\text{m}$
B	70-100 mm	20 mm	$26 \times 42\ \mu\text{m}^2$	$\lesssim 7\ \mu\text{m}$
C	100-130 mm	26 mm	$26 \times 54\ \mu\text{m}^2$	$\lesssim 8\ \mu\text{m}$
D	130-160 mm	32 mm	$26 \times 67\ \mu\text{m}^2$	$\lesssim 9\ \mu\text{m}$



- Pending questions:** * Stitching ? * Challenging system integration

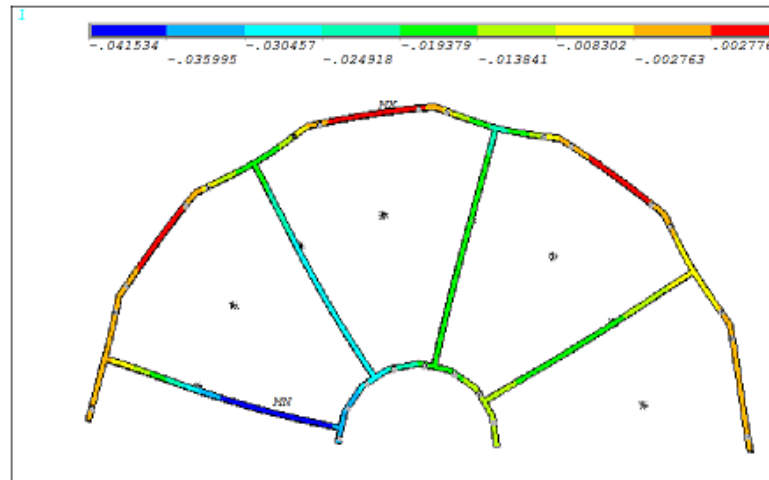
Strip pixels: Module design & Support

- Baseline sensor: conventional microstrip sensor with integrated signal routing in a second metal layer.
- Baseline operational unit: petal (sensor+standard hybrid board(s) with readout, powering and data link circuitry).



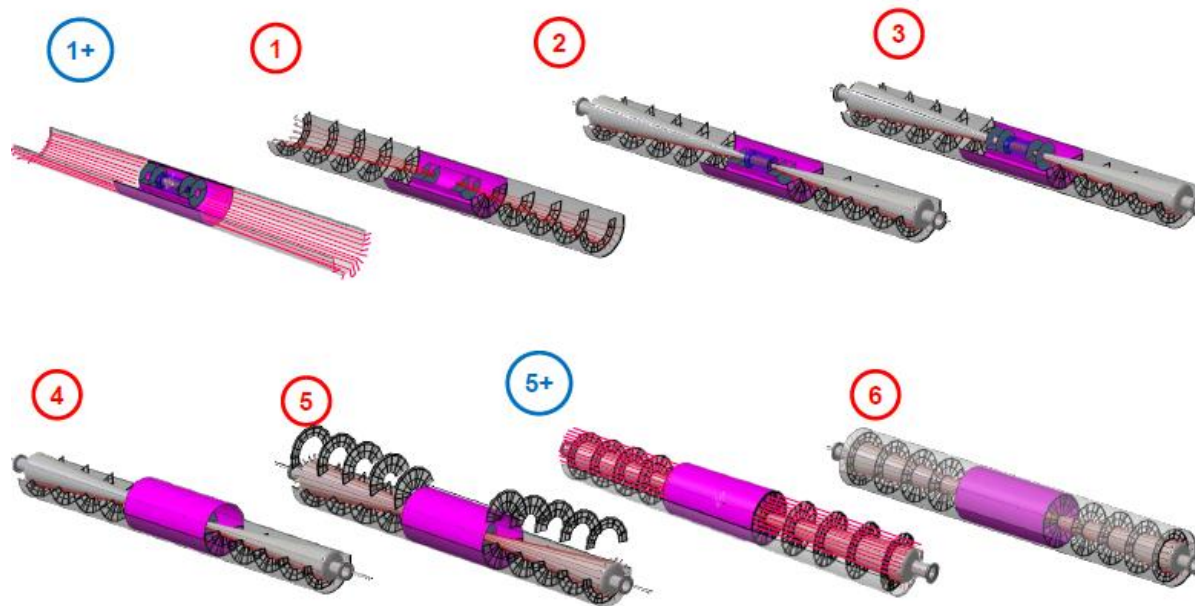
FEA Studies: Stability, Rigidity and Thermal management studies

- Still in a preliminary phase.
- Defining the fixation points and its nature.
- Building the thermal model.
- Thermal loads: Quantifying the thermal sources (R/O chips, optical link, power devices, sensors,...).
- Thermal material characteristic (conductivity, CTE,...)



Mechanics: Integration and Services

- Cabling requirements available for strips FTD.
- Cabling required by pixel FTD extrapolated from VTX.
- Assembly & Integration procedure of FTD fixed.



- In AIDA-WP9 a readout chip for Si-microstrips for ILD is being developed by UB with 65nm process

- ✓ Designed:

- T indep current source*

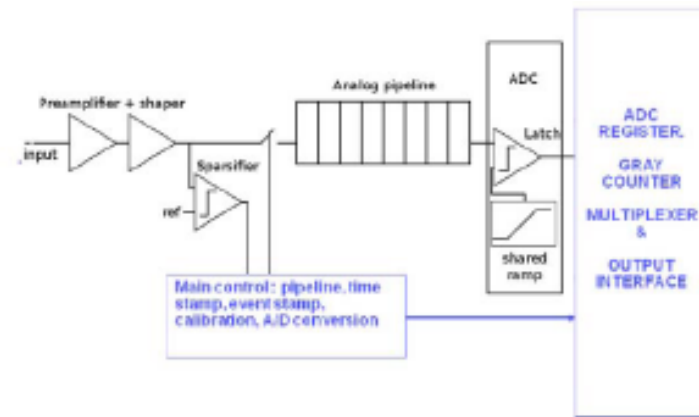
- Amplifier in the preamplifier

- Preamplifier, shaper

- To be designed

- Analog pipeline, Ramp or SAR ADC,

- Discriminator, sparsifier, digital logic, I2C/SPI, LVDS, ...



Concurrent designs with 65nm process:

- 65nm process is used in the development of the DHP together with Bonn Univ. in the framework of DEPFET collaboration for Belle II

- ✓ Designed, fabricated and tested:

- T indep current sources, current-mode DAC*

- Designed

- T sensor



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Powering schemes

- The amount of current required by Strip-FTD is around 650 A
- The ILC accelerator has a duty cycle of 0.5%
 - 1 ms bunch train every 200ms
- If the power demanded by the FEE is synchronized with the bunch train, it helps save energy
 - Dissipated energy will be lower
- The total Strip-FTD current demanded per bunch crossing (a peak current) is 650 A
 - Average current 6.5 A. per cycle (no bunch–no power) .
- However several important issues have to be considered during the design of the power system:
 - Transient phenomena
 - EMI phenomena

Powering schemes (2)

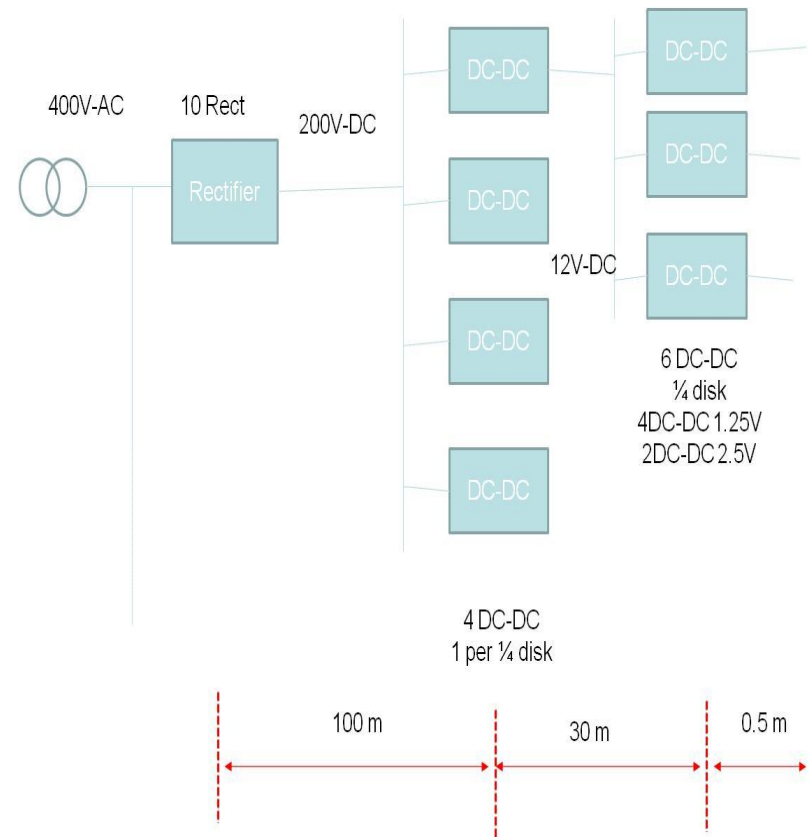


- All these phenomena have an impact on the design of the power supply distribution system
 - _ Topology
 - _ Cooling and material budget
- There are several topologies that may be implemented in the FTD.
 - _ **DC-DC-based power distribution (baseline)**
 - _ Supercapacitor based power distribution (beyond baseline)
 - _ Each of them has advantages and disadvantages
 - _ Both systems are under study.

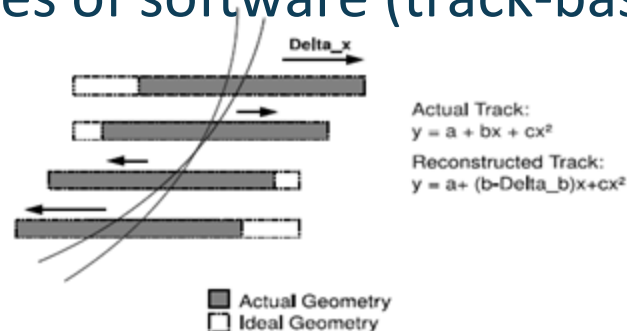
Powering schemes: DC-DC-based Power System



- To absorb transients related to power pulsing system.
 - Keep transients locally at FEE level.
 - Low currents before DC-DC due to converter ratio
 - Low transients
- Synergy with SLHC and new DC-DC hard-Rad design.
 - HF noise & Rad issues



- Current and future silicon systems need for:
 - Real-time monitoring of environment variables: temperature, humidity, CO₂, magnetic field, etc.
 - Real time structural monitoring: deformations, vibrations (push & pull operation), movements.
- Conventional monitoring technologies based on electric relatively bulky transducers with low multiplexing capability, low granularity, and copper readout and powering lines (conductive EM noise propagation lines).
- First lesson from LHC detectors: position and deformation monitors must cover the weak modes of software (track-based) alignment algorithms.

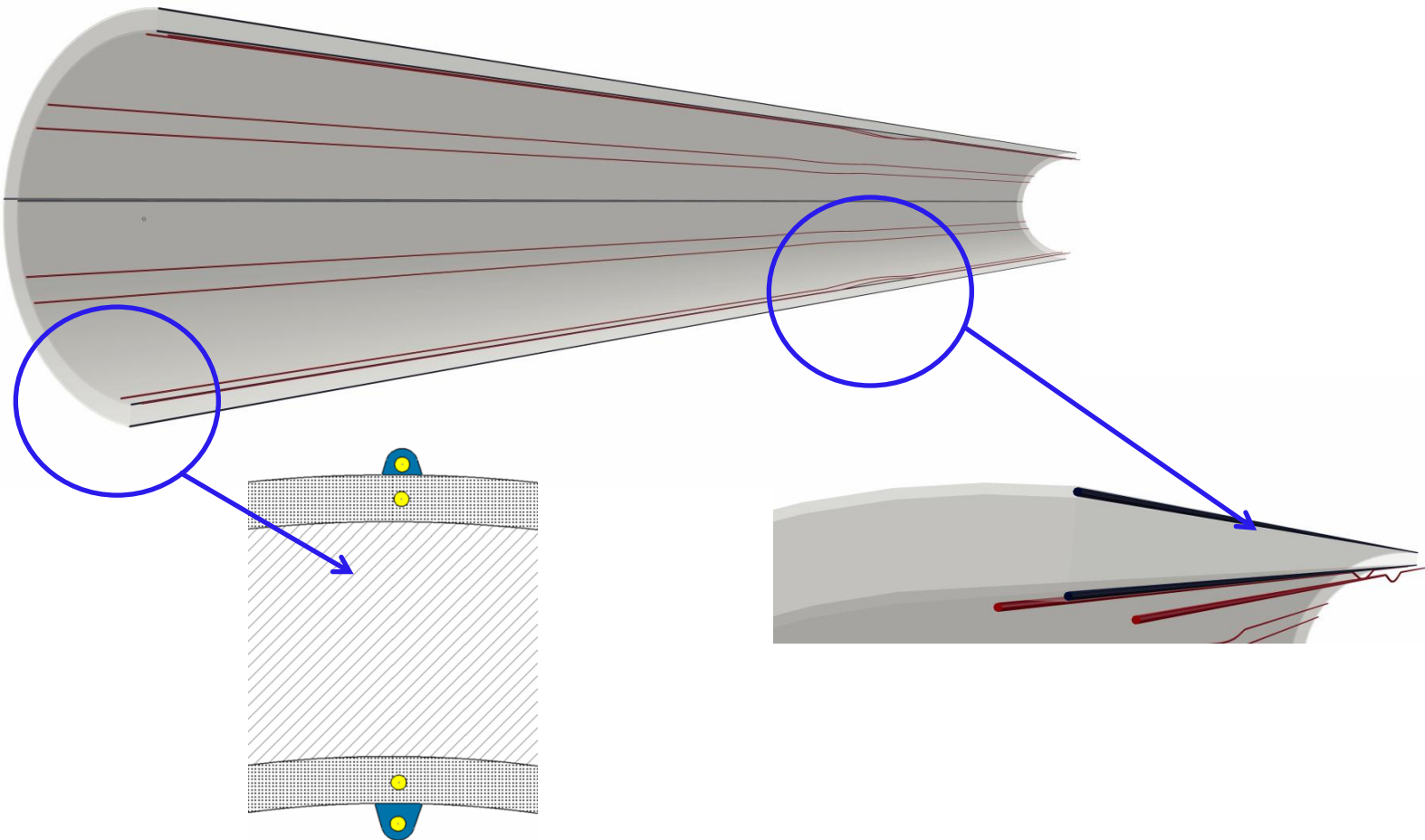


_Introduction to OFS



- Well know monitoring technologies in aeronautics and civil works based on optical fiber sensors (OFS)
- Distributed **strain & temperature** sensors are conventionally used for structure health monitoring : *SMART structures*
- Other OFS: dosimetry, humidity, B field, acceleration, etc.
- In aeronautics (embedded or bonded) on the of the CFRP composite (for instance, plane radar radome)

Instrumentation of the CFRP cover (Inner Detector Supporting Cylinder)



Beyond the baseline

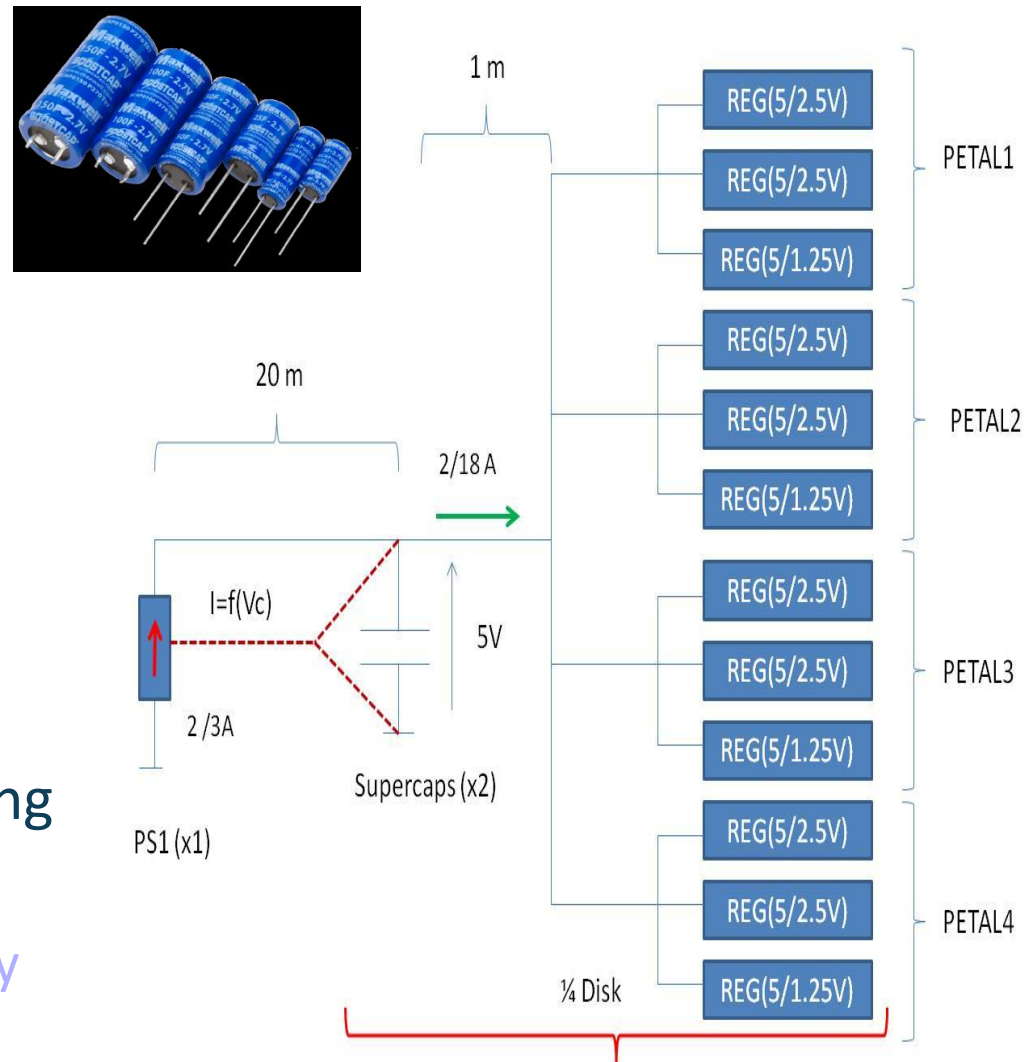


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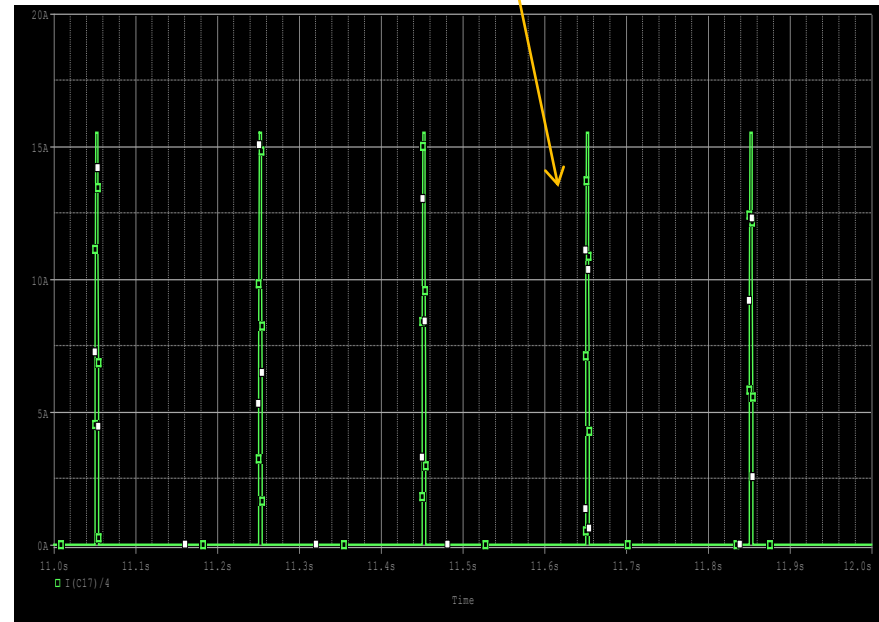
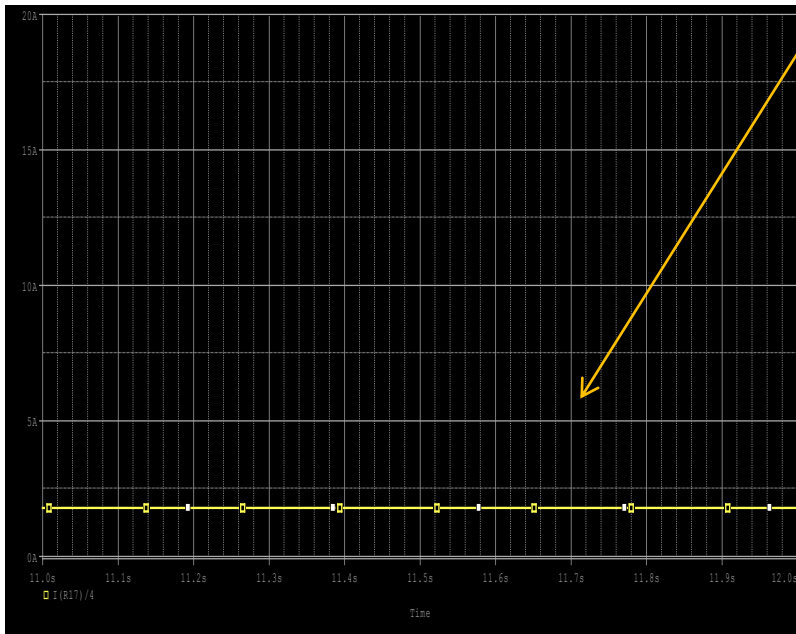
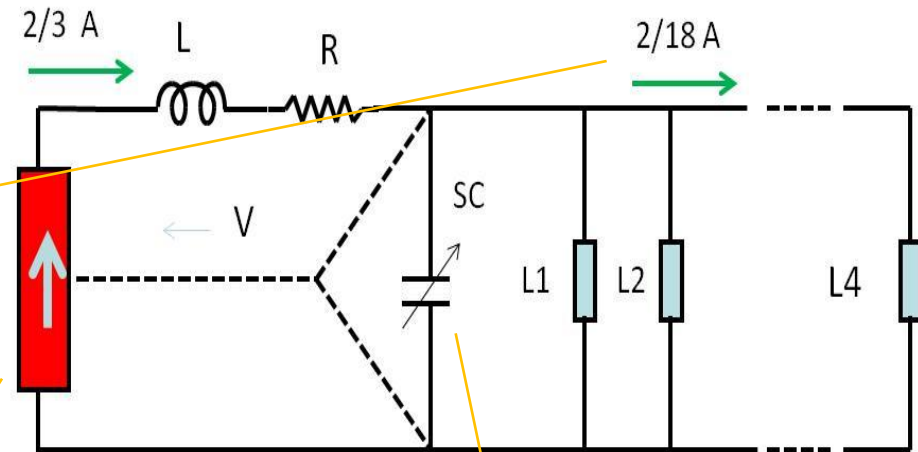
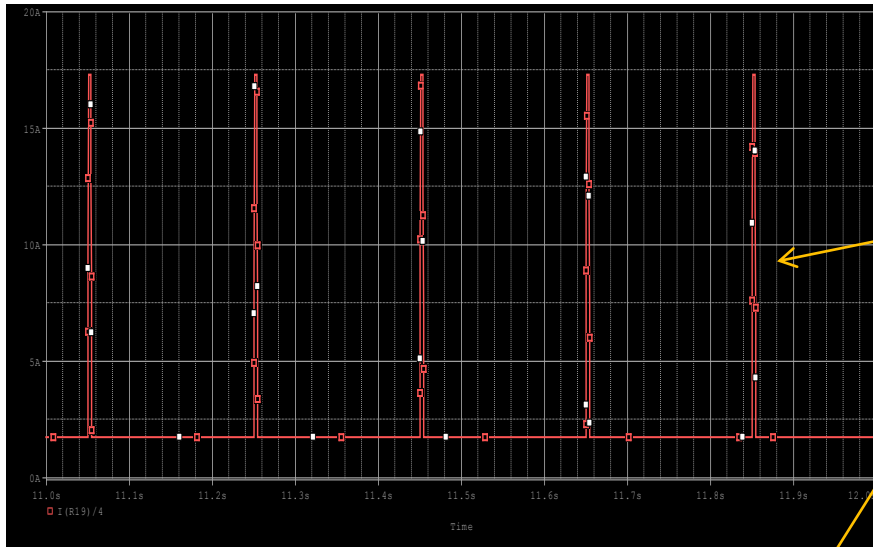
- R&D lines to enhance the detector performance.
- Noiseless and lighter power supply based on supercapacitors.
- Strip sensors providing 2D information:
 - _ Further radial segmentation of the strips.
 - _ Resistive collecting electrodes for charge division method implementation in strips.
- Real time position monitoring:
 - _ Displacement sensors based on FOS FBG sensors.
 - _ Laser-based position monitoring

Powering schemes: Supercapacitor based PS

- This power system is based on :
 - Supercapacitors
 - Pulse power
 - LV regulators
 - Stabilize FEE voltage
 - Current source
 - supercapacitor voltage controlled
- To absorb transients related to power pulsing system.
 - Keep transients locally at FEE level.



Powering schemes: Supercapacitor based PS



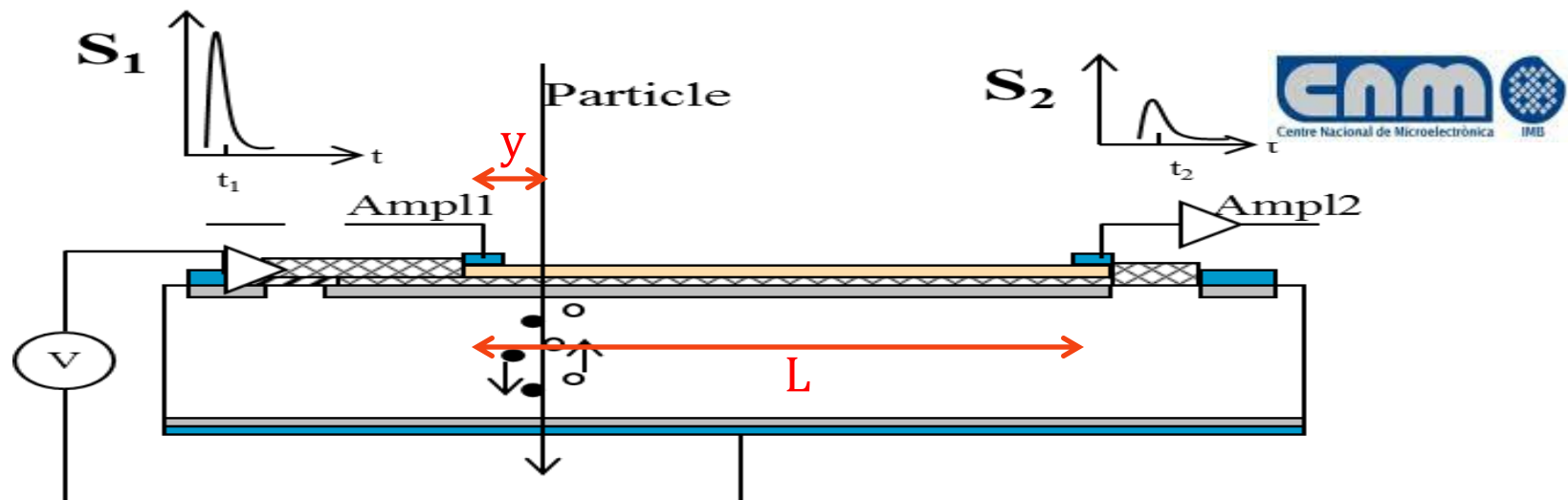
Powering schemes: Supercapacitor based PS



- The most important element is the supercapacitor.
 - It is new for HEP but not for industrial applications
- There are two elements that have to be analyzed in detail for HEP applications
 - Radiation issues
 - Cycling issues.
- Radiation issues
 - Type of radiation: Gamma & electrons
 - Total dose : around 2 MRad.
- Cycling issues (Reliability).
 - Supercapacitor should be able to operate more that 10 million cycles per year
- A detailed test plan is on going to study both effects

Charge-Division Concept in ustrip Sensors

- Charge division used in wire chambers to determine the coordinate along the sensing wire.
- Same concept with conventional microstrips with slightly resistive electrodes (doped polysilicon)



$$\text{Fractional Position} \equiv y/L = S_2/(S_1 + S_2)$$

New Prototypes from CNM

- One year ago very promising results on CNM's first prototypes with integrated on sensor signal routing for single-end readout (affected by parasitic couplings, see later in this talk).
- Now presenting results on two new prototypes with double-end readout.

Strip:

length =20 mm

width =20 μm

Pitches:

Implant=80 μm

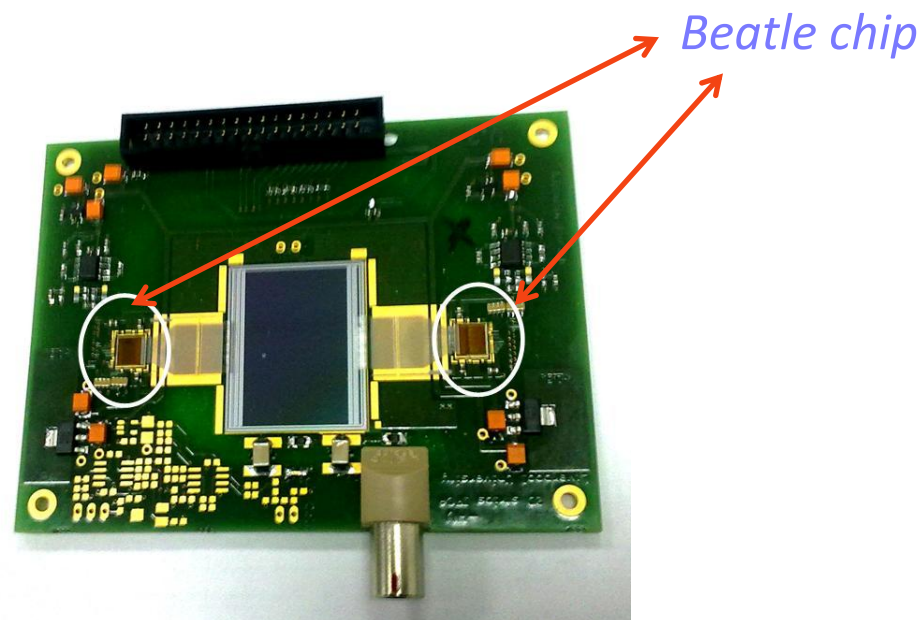
readout= 80 μm

Electrode:

$R/\mu\text{m} = 2.8 \text{ Ohms}/\mu\text{m}$

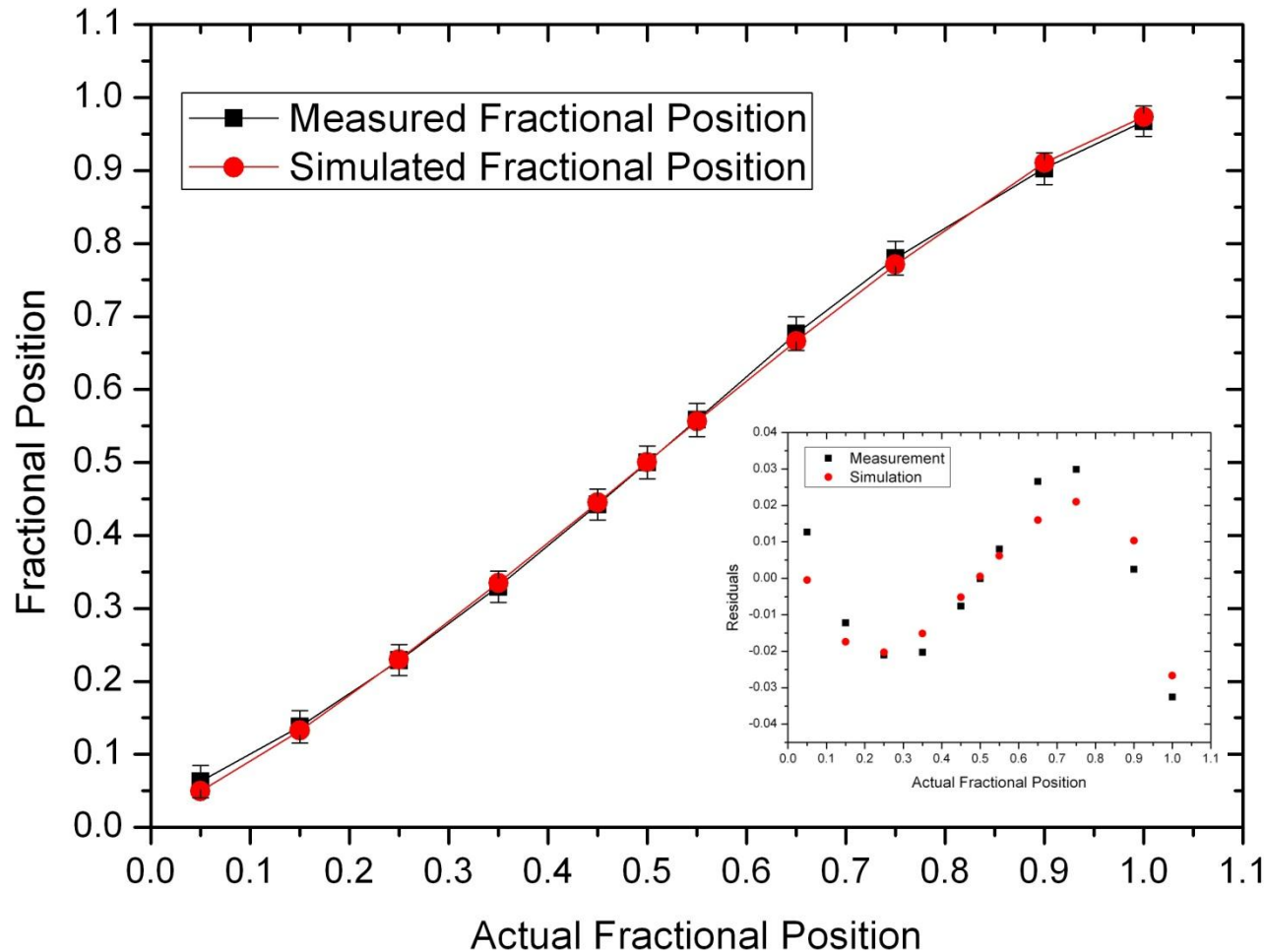
$R/\mu\text{m} = 12.2$

$\text{Ohms}/\mu\text{m}$

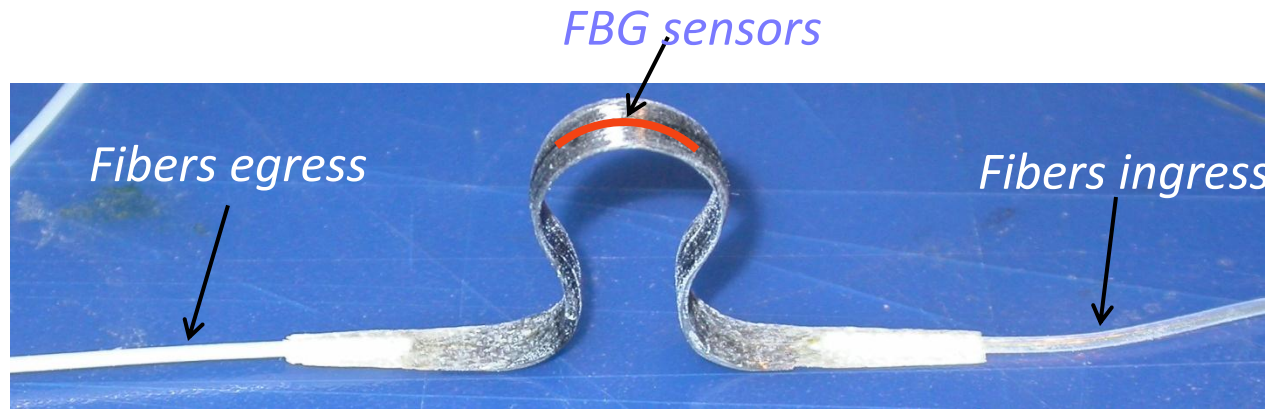


Data vs. Simulation: Fractional position (1)

– High resistivity sensor: $12.2 \Omega/\mu\text{m}$, $RC = 450\text{ns}$



Miniaturized ultra-light linear position transducer



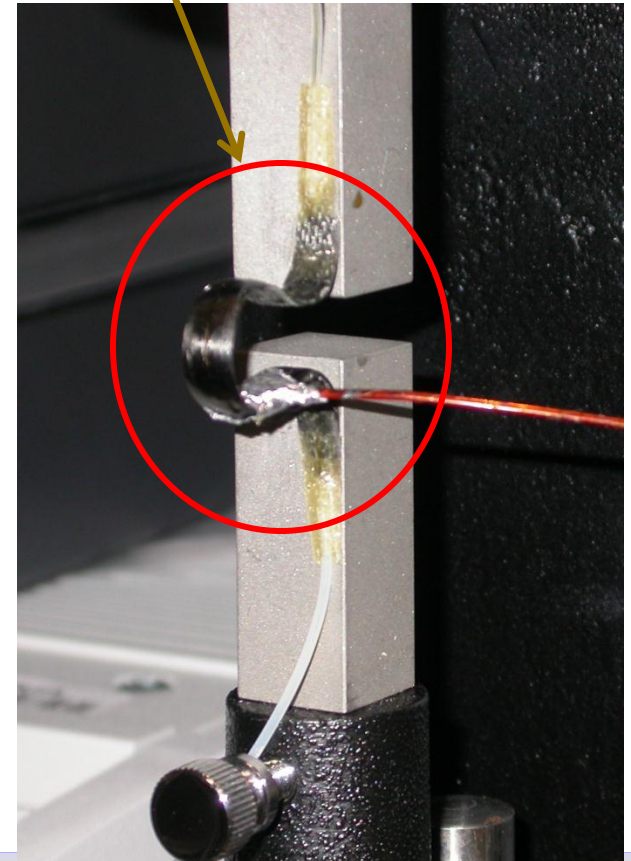
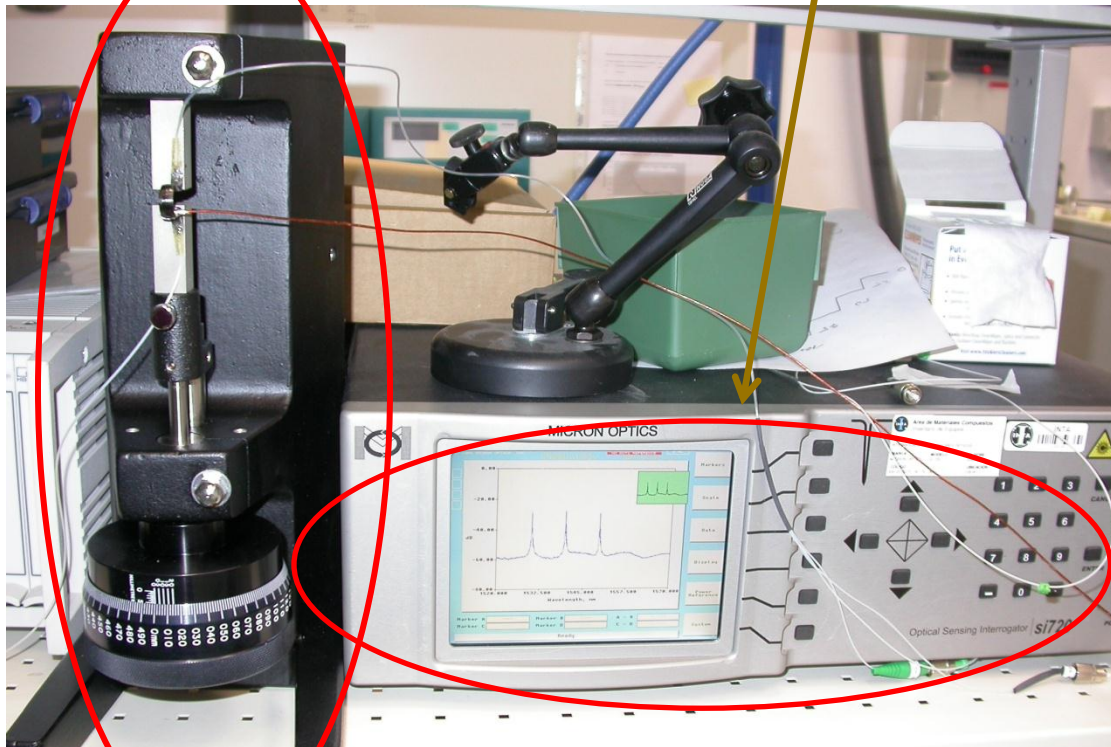
- Two sensors are positioned in the outer and inner layer of the omega (point of maximum strain / maximum resolution)
- One sensor in the middle layer to compensate temperature (point of minimum strain)
- The temperature can be compensated with the difference in the measurement of bottom and top sensor)

Results on first Omega Prototypes

Micrometric Stage

FBG sensor
interrogation unit

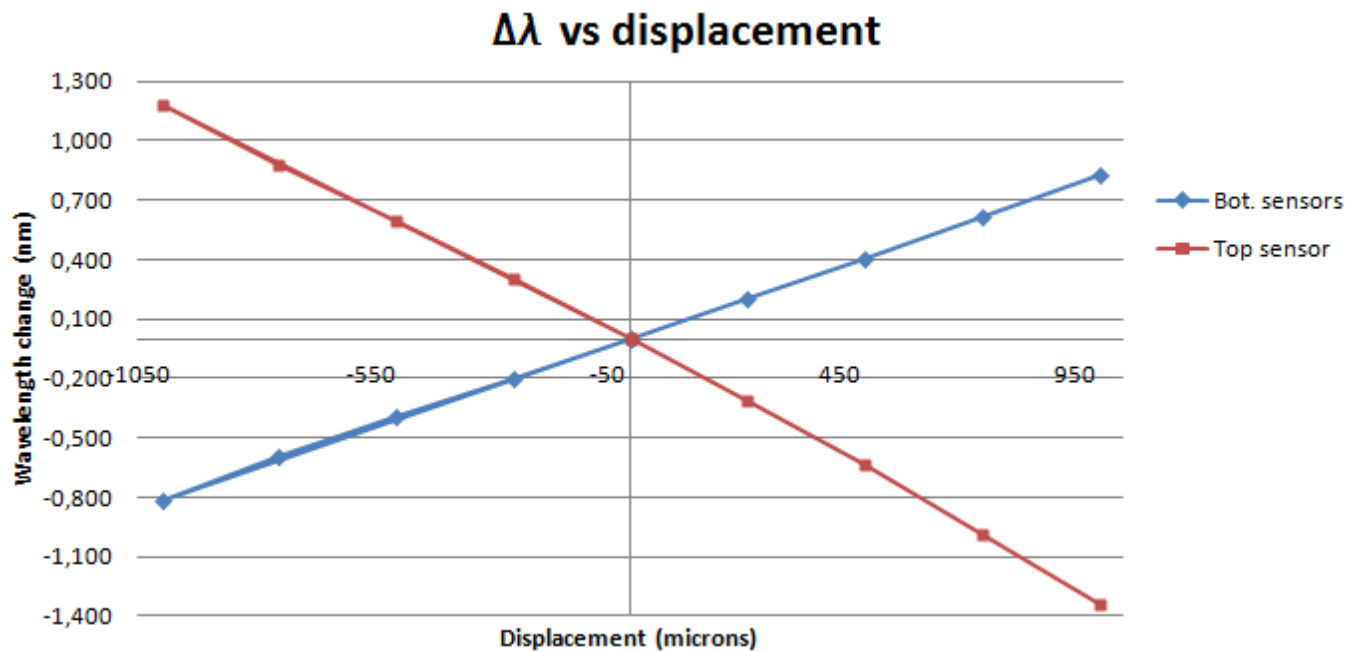
Omega



_Omega First measurements

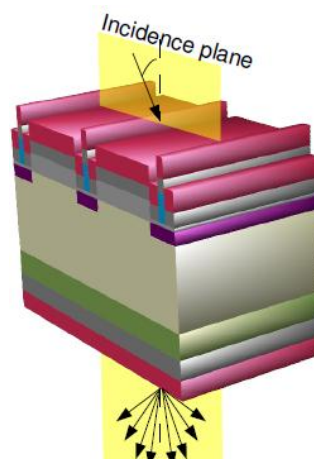
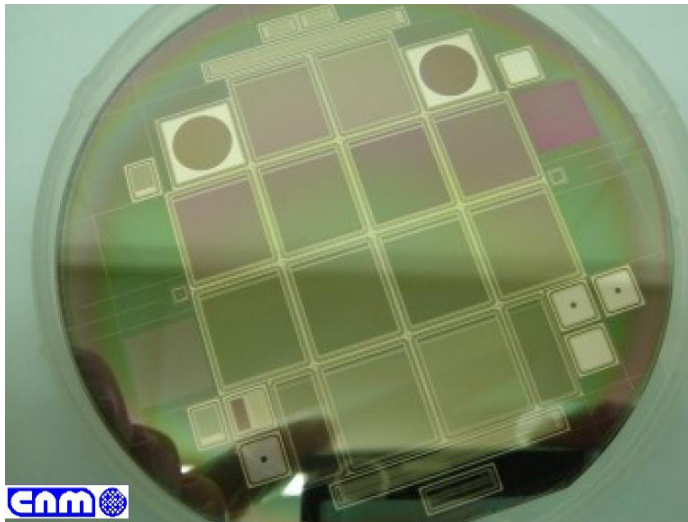


- The obtained displacement resolution is of 0.5 μm
- The relation is lineal in the range +1mm to -1 mm
- The temperature can be compensated by difference between the top and bottom sensor
- The omega will be tested in Santander again to measure the reaction and have redundancy in the results obtained.

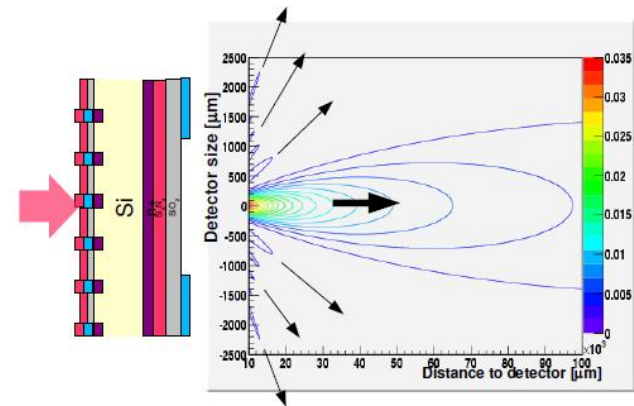


Real time Relative position monitoring of FTD forward-backward halves (2)

- Optical optimized strip sensors developed within EUDET FP7 project (transparency tunned using the estándar fabrication process)



Including diffractive effects



Summary



- Baseline design based on 100% standard and available technologies.
- Additional R&D lines on:
 - _ Front-end electronics
 - _ Power supply (Supercapacitors based)
 - _ 2D resistive strip sensors
 - _ FOS-based Miniaturized hard-rad linear displacement transducers.
 - _ Semitransparent alignment strips sensors.

GRACIAS



BACK

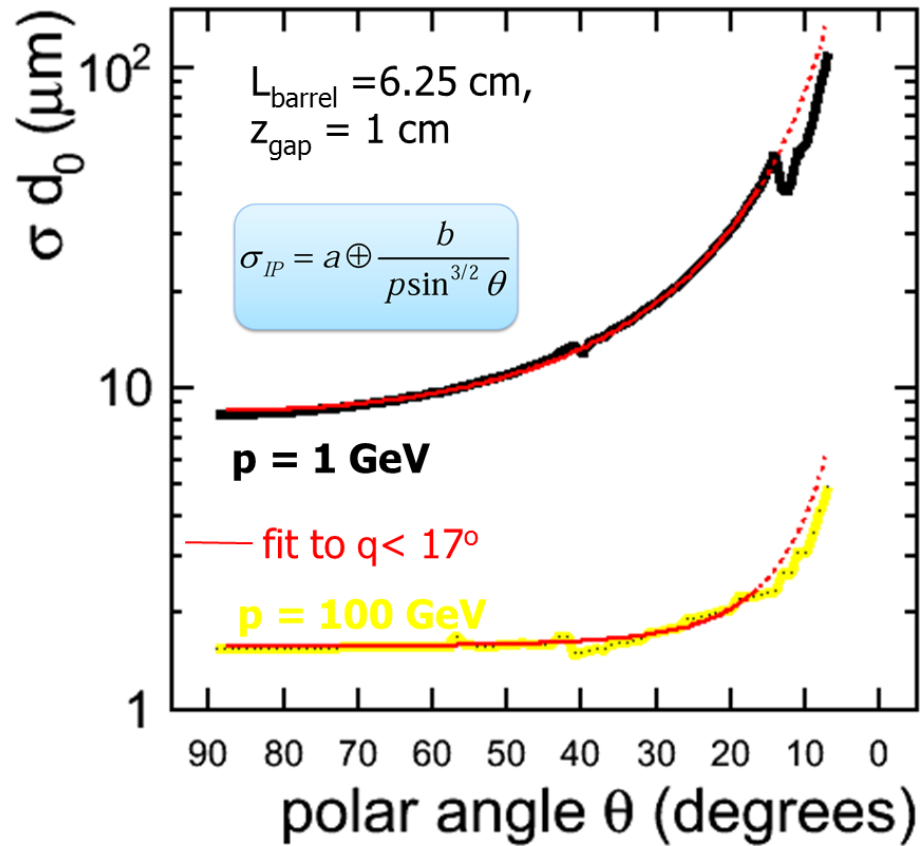
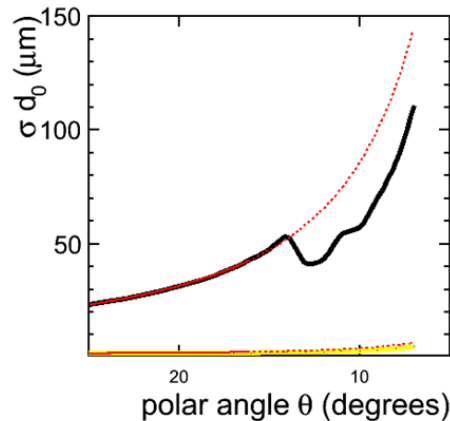
UP

Transverse impact parameter resolution

Transverse impact parameter resolution vs. polar angle

Barrel-dominated part well-described by the standard formula.

Deviations in the very forward region (as expected)



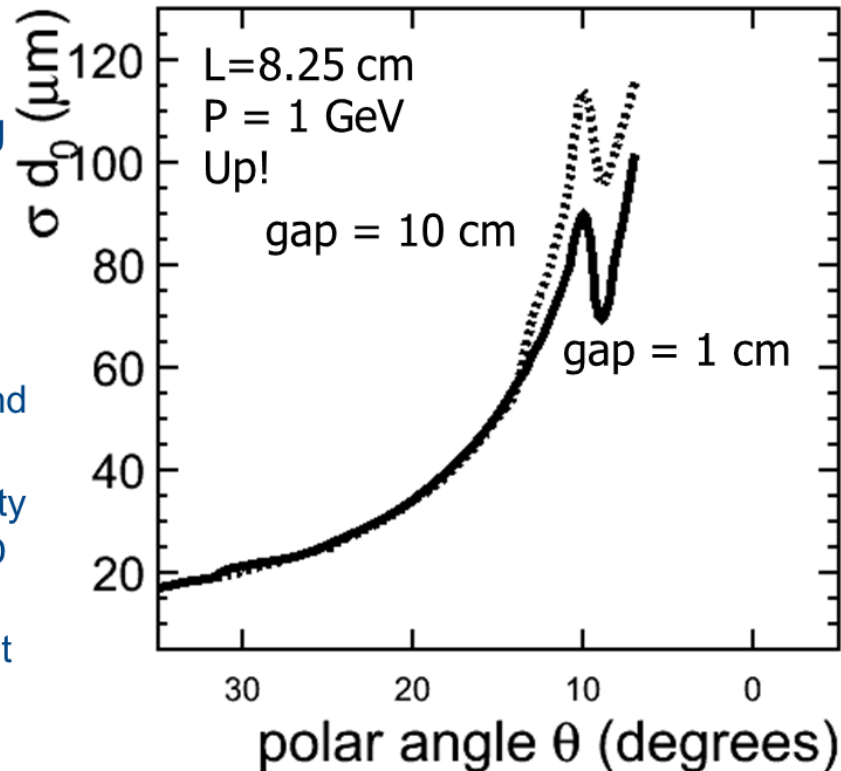
Zgap between the FTD1 and VTX

Comparison z_{gap}

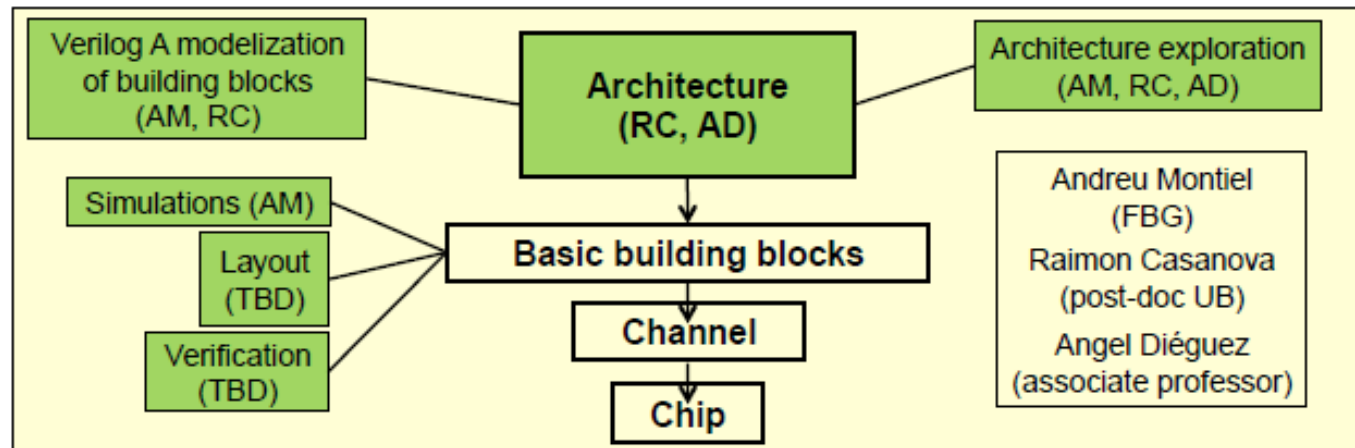
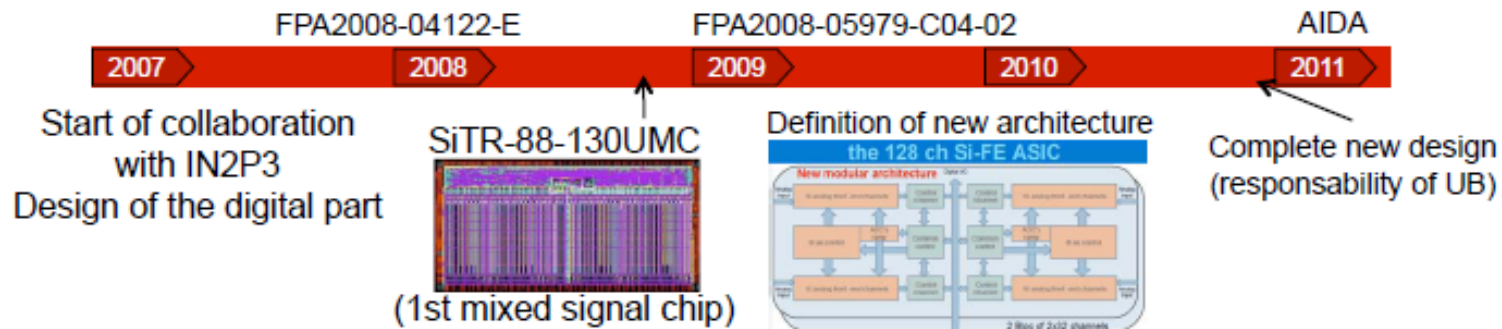
Minimize the gap! *

But: if we route the services along the beam pipe, the forward vertexing performance is terrible and essentially insensitive to z_{gap}

* In ILD the distance between VXD and innermost FTD is close to 10 cm. This clearance is motivated by the possibility to fit in a VXD cryostat. If a “cold” VXD technology is chosen, a short gap implies one has to install the innermost disks inside the cryostat.



Front-end Electronics: new approach



AIDA

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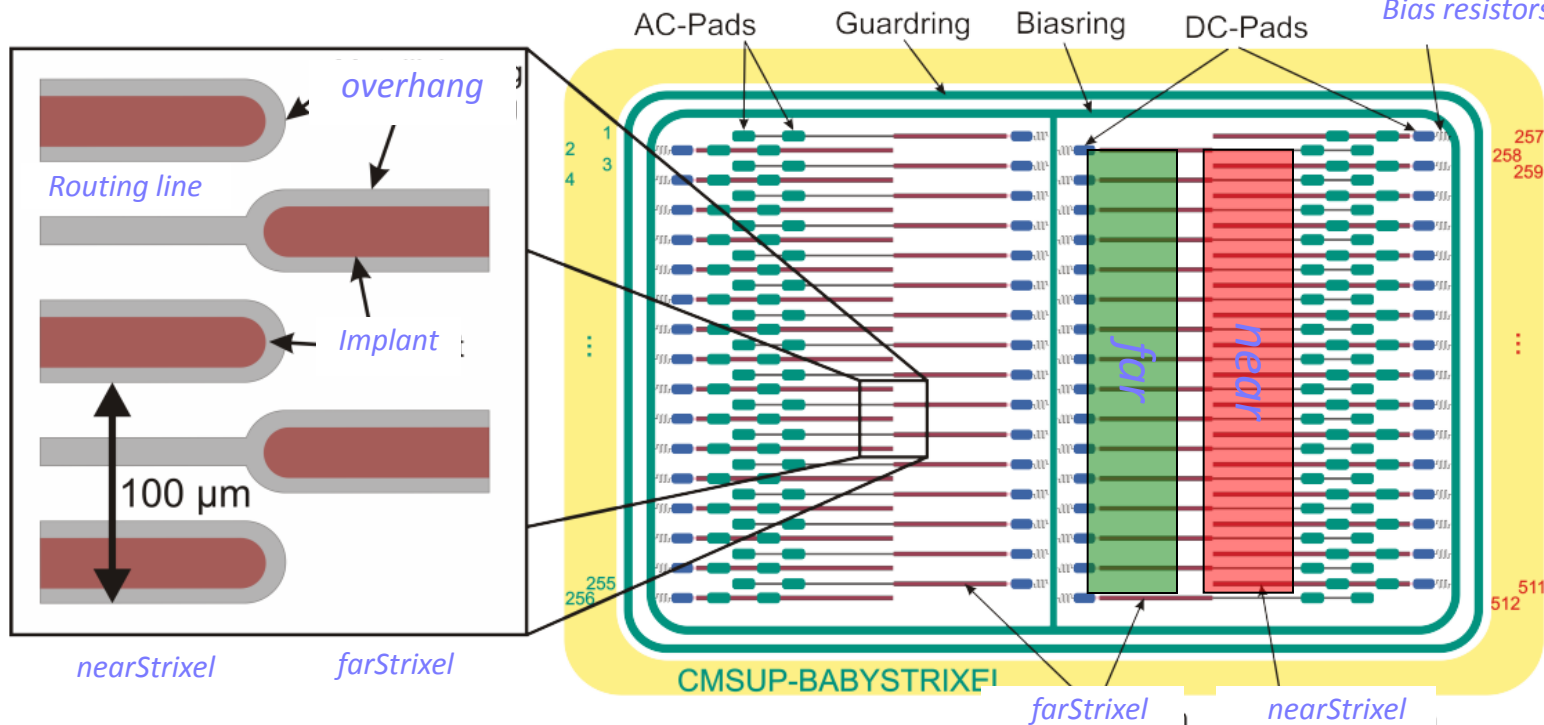


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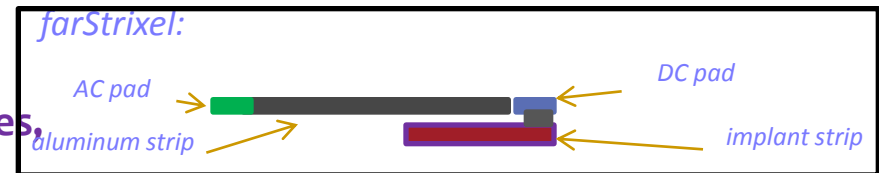
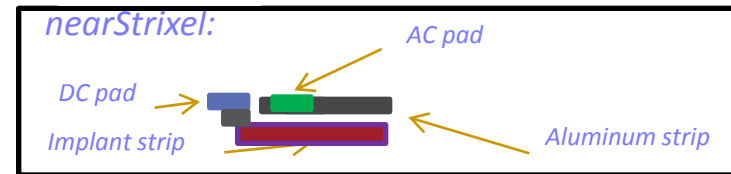


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Stripxels – schematic overview



- increases granularity by a factor of 4
- readout at the sensor edges
- Distinguish between **near** and **far** region (nearStrixel / farStrixel)



ivan.vila@csic.es, IX Jornadas Futuros Aceleradores,
Dec 18th, IFIC.

2.1 Powering schemes: DC-DC-based Power System

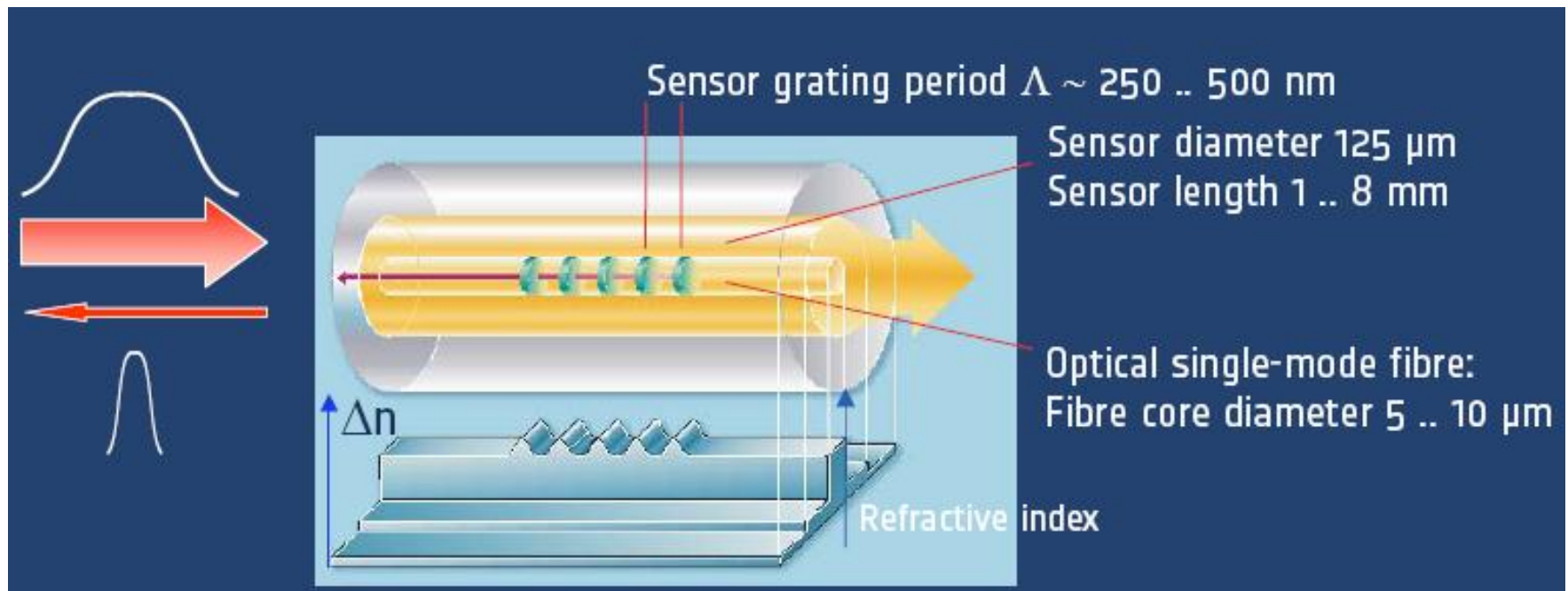


- Example (1/4 disk) : Power values per group:
 - Routing inside each petal:
 - 6 DC-DC converters
 - 4 DC-DC (12V - 2.5V)
 - 2 DC-DC (12V- 1.25V)
 - Max out current per DC-DC less than 3 A (low transients)
 - Short cabling – Less than 1 meter (low voltage drop)
 - Outside petal (1 cable per ¼ disk)
 - 1 DC-DC per power group
 - 200V – 12V
 - Max out current per DC-DC less than 3 A
 - Transients attenuated by the DC-DC
 - Outside experiment
 - 1 AC-DC per disk
 - 400V 50 Hz – 200V DC
 - Max current per cable less than 1 A

Fiber Bragg Grating Optic Sensor 101



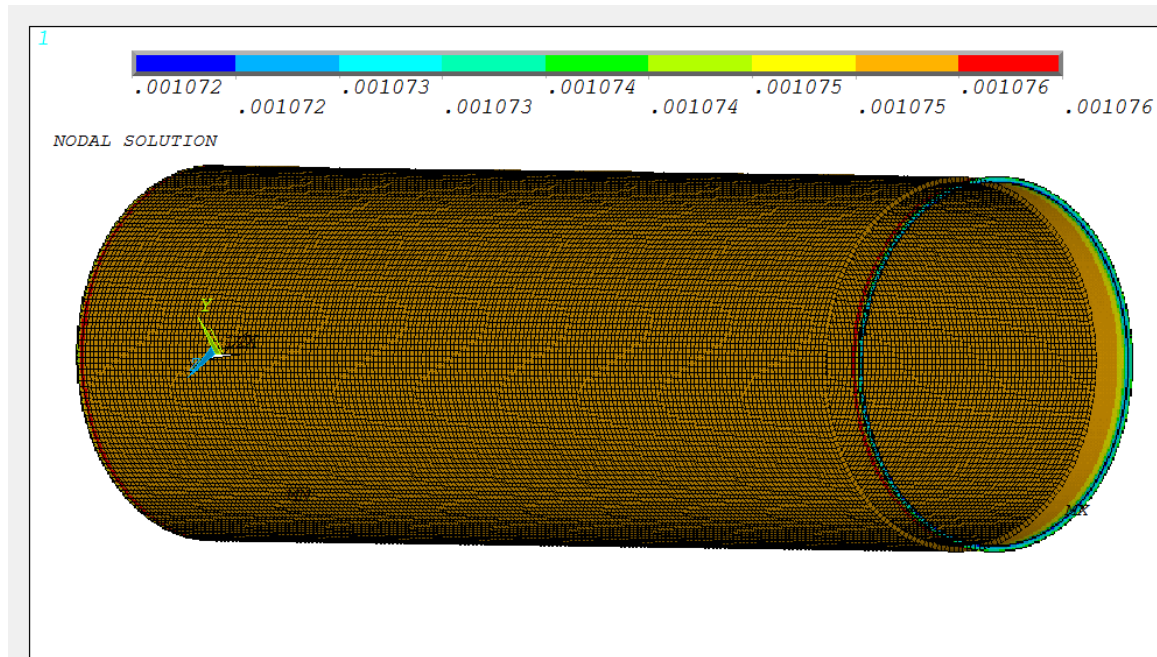
- Keep in mind: Physically, FGB sensors have a section of an optical fiber with a length of few millimeters.



Monitoring of CFRP cover deformation



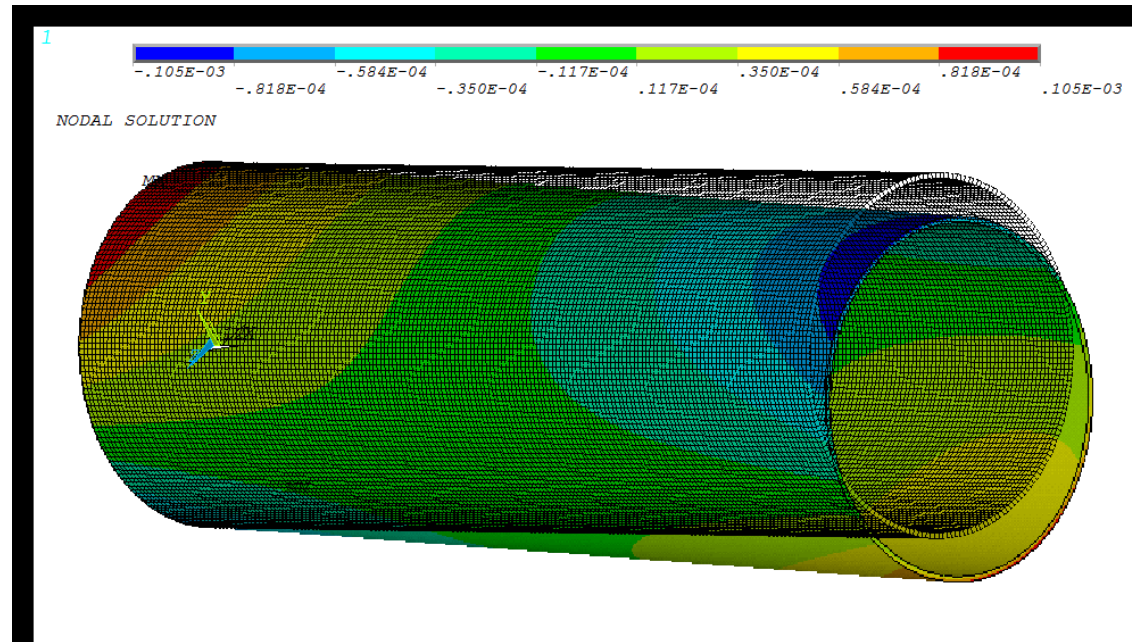
- Name of the game: extract cover deformations out of FBG readout.



Z(mm)	0	60	120	180	240	300
20	1,075E-03	1,075E-03	1,075E-03	1,075E-03	1,075E-03	1,075E-03
465	1,075E-03	1,075E-03	1,075E-03	1,075E-03	1,075E-03	1,075E-03
910	1,075E-03	1,075E-03	1,075E-03	1,075E-03	1,075E-03	1,075E-03

Monitoring of CFRP cover deformation (2)

- Relative movement between cylinder end flanges.



Z(mm)	0	60	120	180	240	300
20	-1,535E-06	-8,455E-05	-1,535E-06	8,302E-05	8,302E-05	9,294E-12
465	-1,979E-07	-1,725E-10	-5,479E-15	6,246E-15	-1,500E-14	5,559E-06
910	-1,500E-06	8,112E-05	8,112E-05	-1,500E-06	-8,112E-05	-3,840E-05

FOS for environmental and structural monitoring industry driven technology



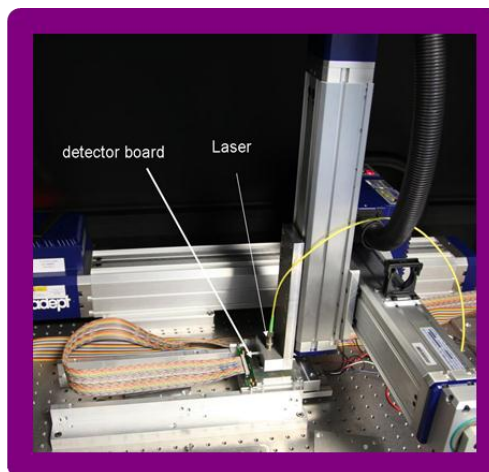
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NIR laser test stand

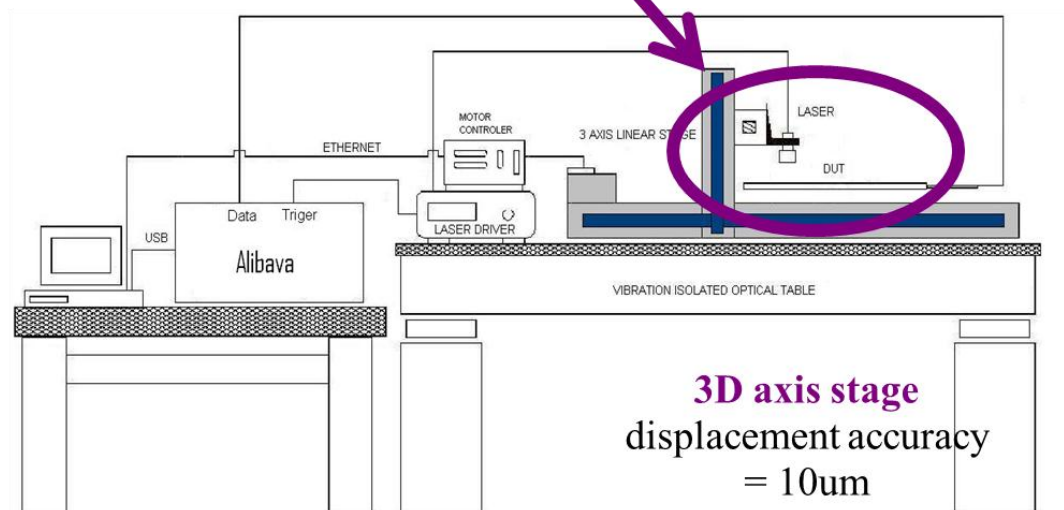
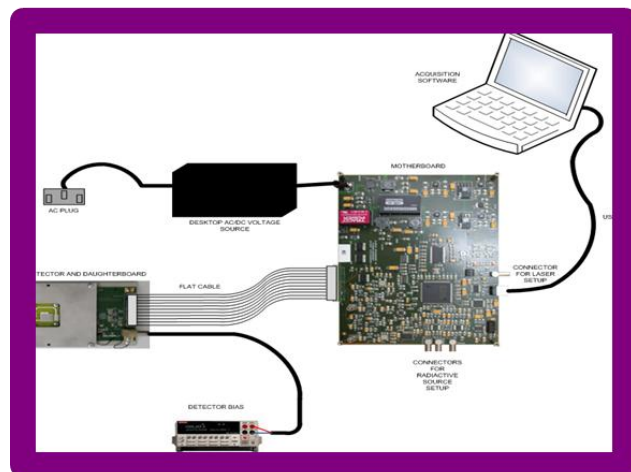
ALIBAVA DAQ system

- * Beetle readout chip
- * 256 channels
- * peaking time ~ 25 ns
- * S/N ~ 20 (standard and non irradiated detectors)



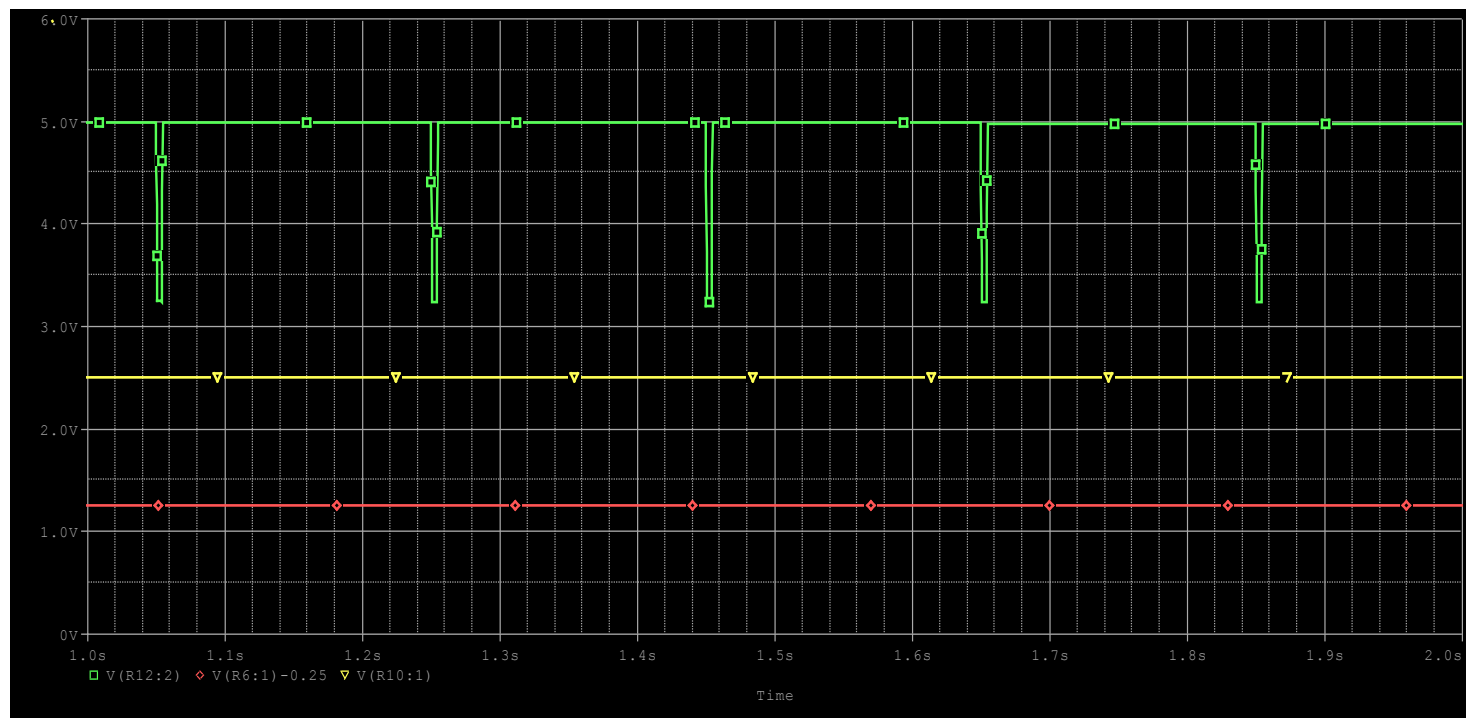
Pulsed DFB laser $\lambda=1060\text{nm}$

- gaussian beam spot width $\approx 20 \mu\text{m}$
- rise time 2ns
- **total charge $\approx 5\text{-}10$ MIPs**



Powering schemes: Supercapacitor based PS

- Each pulse generates a voltage dip
 - It is mainly influenced by the ESR of the supercapacitor
Line impedance, too.
- Transient can be easily absorbed by the LV regulator
 - It should be a RAD tolerant component



Powering schemes: Supercapacitor based PS



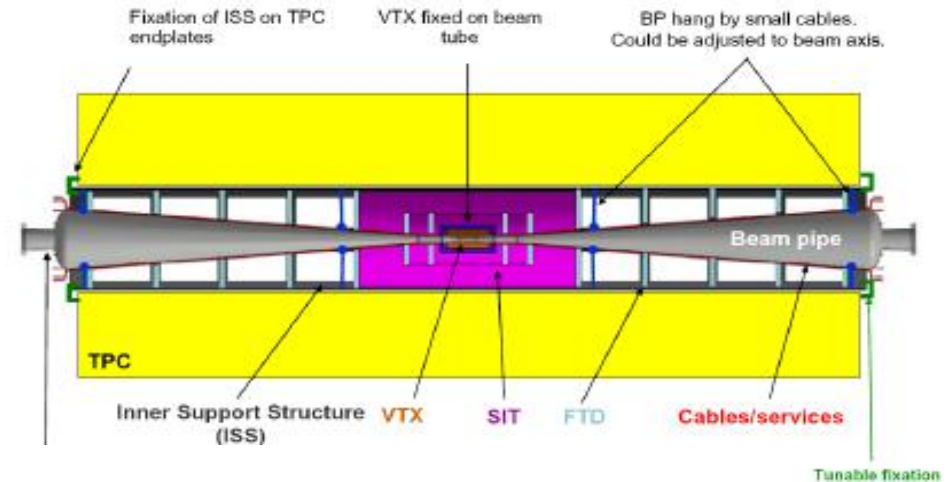
- Power values per $\frac{1}{4}$ disk (power group)
 - Routing inside each petal
 - 3 Regulators
 - 2 REG (5V -2.5V) / 2.92 A Pk – 0.29A
 - 1 REG (5V- 1.25V) / 1.42 A Pk – 0.15A
 - Max out current per petal (16 petals) – 4.34 A / 0.434A
 - Short cabling – Less than 1 meter (low voltage drop) ?
 - 2 Supercapacitors per (1/4 disk) – C=75 F / V=5 V / I_{max}=18 A / I_{min}=2
 - Outside petal - $\frac{1}{4}$ disk
 - 1 Cable per disk
 - Max out current per cable around 2/3 A (defined by FEE)
 - Outside experiment
 - 1 Current source per $\frac{1}{4}$ disk
 - IDC = 2/3 A
- A similar number of HV cable will be considered to keep the same granularity
 - 1 HV cable and HV power unit per $\frac{1}{4}$ disk

Future plans for power issues

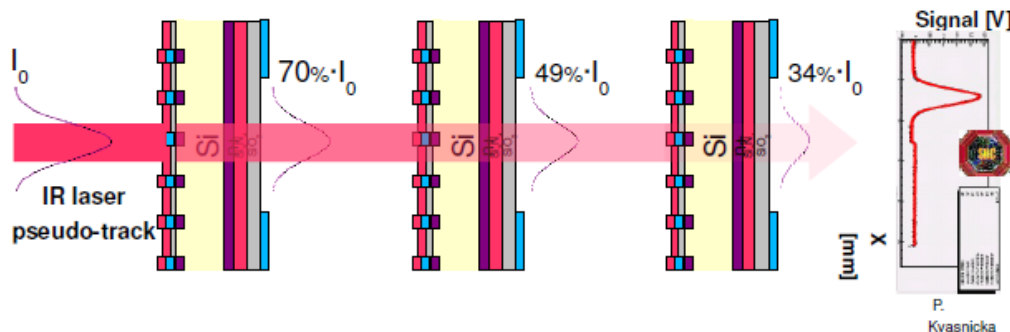


- A comparative analysis of power dissipation of both DC-DC based and supercapacitor based power systems
- Supercapacitor option :
 - Radiation effects on supercapacitor : Test campaign
 - Reliability issues : Power cycling effects
- DC-DC option:
 - It is planned to follow the CERN group development of RAD and magnetic field tolerant DC-DC converters.
 - Power cycling effects

Real time Relative position monitoring of FTD forward-backward halves.



- Laser tracks can be used by a hardware system to align the tracker



- First implemented by AMS I, then AMS II and CMS